

F1 *Sub I 2*
79. (Twice Amended) A device according to claim 78 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F2 *Sub I 1*
85. (Twice Amended) A device according to claim 84 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F3 *Sub I 2*
91. (Twice Amended) A device according to claim 90 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F4 *Sub I 1*
97. (Twice Amended) A device according to claim 96 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F5
105. (Twice Amended) A device according to claim 102 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F6 Sub 126

113. (Twice Amended) A device according to claim 110 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F7 Sub 130

121. (Twice Amended) A device according to claim 118 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F8 Sub 131

129. (Twice Amended) A device according to claim 126 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F9 Sub 136

135. (Twice Amended) A device according to claim 134 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F10 Sub 140

141. (Twice Amended) A device according to claim 140 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.